

N-channel 30 V 3.15 m Ω logic level MOSFET in LFPAK33 using NextPower Technology

Rev. 4 — 15 June 2012

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment

1.2 Features and benefits

- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Load switching

Synchronous buck regulator

1.4 Quick reference data

Table 1. Quick reference data

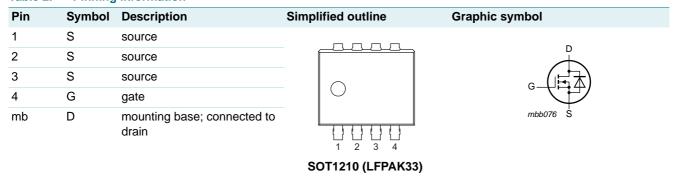
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25 ^{\circ}\text{C}$	-	-	30	V
I_D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u> _	-	70	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	88	W
Tj	junction temperature		-55	-	175	°C
Static charact	eristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 10	-	3.5	4.05	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 10	-	2.7	3.15	mΩ
Dynamic char	acteristics					
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 15 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	4.3	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 15 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	16.1	-	nC

^[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information



3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN3R0-30MLC	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 4 leads	SOT1210		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Mi	n Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	[1] -	70	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u> -	70	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 4	-	498	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	88	W
T _{stg}	storage temperature		-5	5 175	°C
Tj	junction temperature		-5	5 175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	35	0 -	V
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	<u>[1]</u> _	70	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	498	Α
Avalanche ru	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 70 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω; unclamped; see Figure 3	-	64	mJ

^[1] Continuous current is limited by package.

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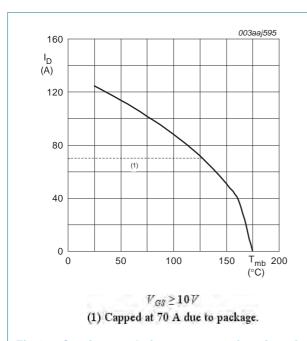


Fig 1. Continuous drain current as a function of mounting base temperature

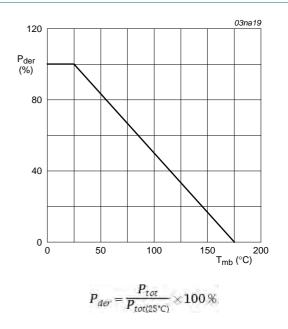


Fig 2. Normalized total power dissipation as a function of mounting base temperature

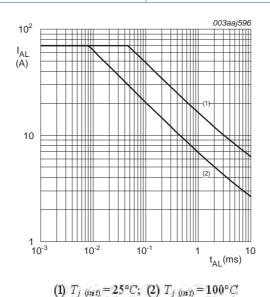
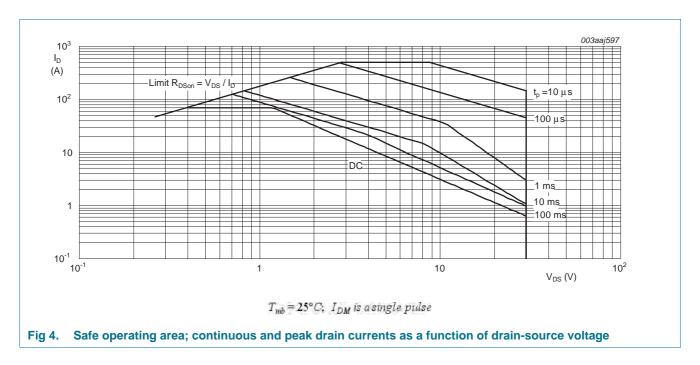


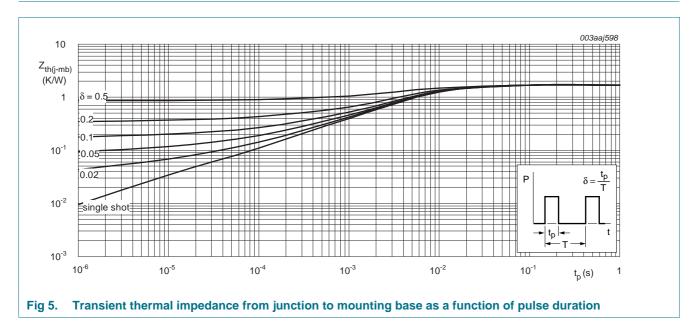
Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from	n junction to mounting base	-	1.49	1.7	K/W
	see Figure 5					



6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics	Conditions	Min	T) /m	May	l lmit
Symbol	Parameter	Conditions	IVIIN	Тур	Max	Unit
	racteristics					
V _{(BR)DSS} drain-source breakdown voltage	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.45	1.74	2.15	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature		-	-4	-	mV/K
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	-	3.5	4.05	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 150 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	6.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	-	2.7	3.15	mΩ
		$V_{GS} = 10 \text{ V}$; $I_D = 25 \text{ A}$; $T_j = 150 \text{ °C}$; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	5.35	mΩ
R_G	gate resistance	f = 1 MHz	0.37	0.74	1.48	Ω
Dynamic c	haracteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 12; see Figure 13	-	34.8	-	nC
		$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; see Figure 12; see Figure 13	-	16.1	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	32.3	-	nC
Q_{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	6.2	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see Figure 12; see Figure 13	-	3.7	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.5	-	nC
Q _{GD}	gate-drain charge		-	4.3	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 15 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	2.9	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	2330	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	480	-	pF
C _{rss}	reverse transfer capacitance		-	180	-	pF

 Table 6.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	V_{DS} = 15 V; R_{L} = 0.6 Ω ; V_{GS} = 4.5 V; $R_{G(ext)}$ = 5 Ω	-	16.2	-	ns
t _r	rise time		-	27.2	-	ns
t _{d(off)}	turn-off delay time		-	18.3	-	ns
t _f	fall time		-	13.7	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 ^{\circ}\text{C}$	-	14.2	-	nC
Source-drai	in diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 15</u>	-	0.8	1.1	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	22.7	-	ns
Q _r	recovered charge	V _{DS} = 15 V	-	17	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V; } I_S = 25 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s;}$ $V_{DS} = 15 \text{ V; see } \frac{\text{Figure 16}}{\text{Im}}$	-	13.7	-	ns
t _b	reverse recovery fall time		-	9	-	ns

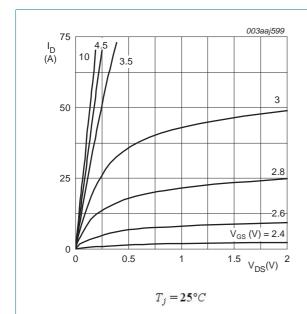


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

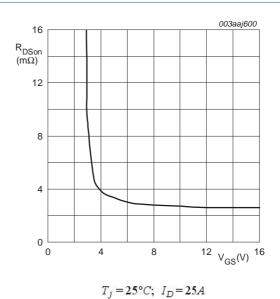


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

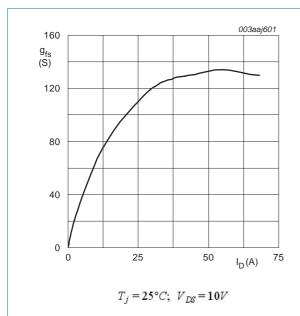


Fig 8. Forward transconductance as a function of drain current; typical values

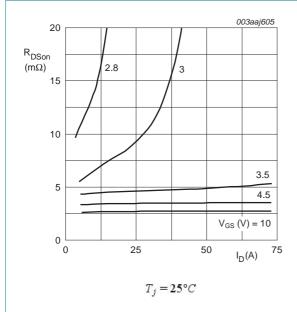


Fig 10. Drain-source on-state resistance as a function of drain current; typical values

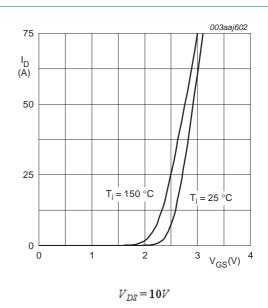


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

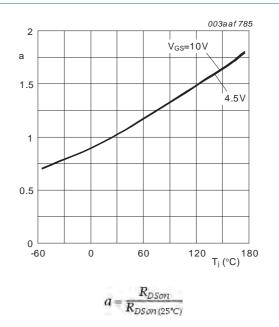


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

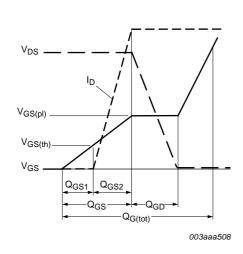


Fig 12. Gate charge waveform definitions

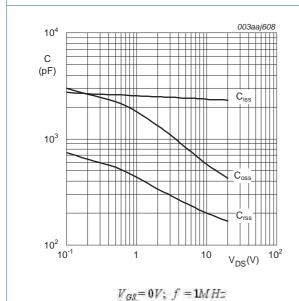


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

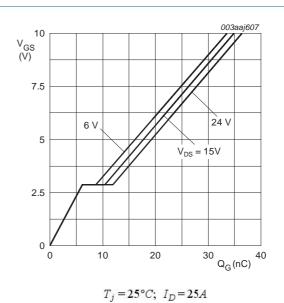


Fig 13. Gate-source voltage as a function of gate charge; typical values

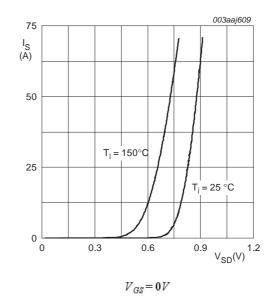
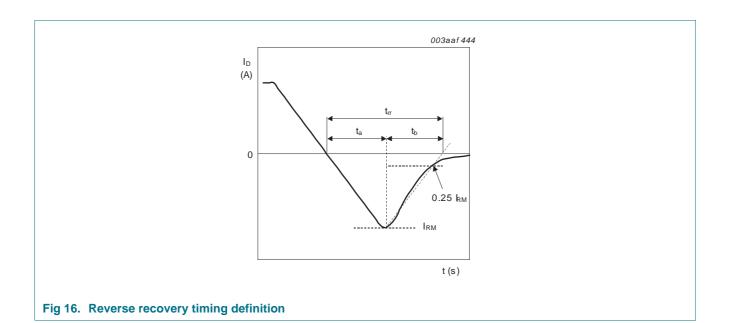


Fig 15. Source current as a function of source-drain voltage; typical values



7. Package outline

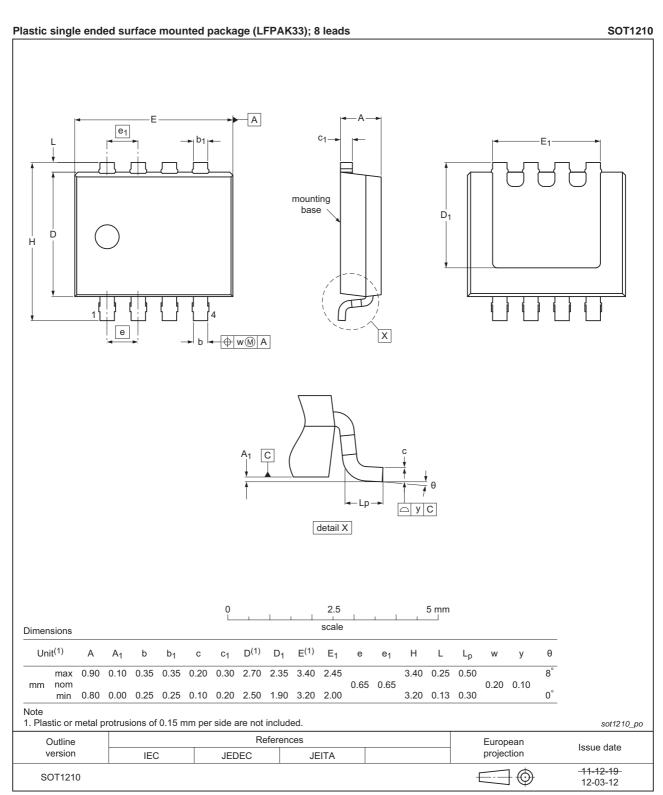


Fig 17. Package outline SOT1210 (LFPAK33)

PSMN3R0-30MLC

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R0-30MLC v.4	20120615	Product data sheet	-	PSMN3R0-30MLC v.3
Modifications:	 Status changed from 	m objective to product.		
	 Various changes to 	content.		
PSMN3R0-30MLC v.3	20120607	Objective data sheet	-	PSMN3R0-30MLC v.2

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9. Legal information

9.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions".
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